YEA SHIN TECHNOLOGY CO., LTD

YS5465BA

P-Channel Enhancement MOSFET

VDS = -60V, ID = -16A

DESCRIPTION

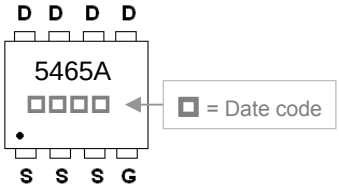
The YS5465BA is the highest performance P-ch MOSFETs with super high dense cell design for extremely low $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The YS5465BA meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

FEATURES

- Low Reverse Transfer Capacitance
- Improved dv/dt Capability
- Green Device Available
- High Switching Speed
- 100% EAS Guaranteed

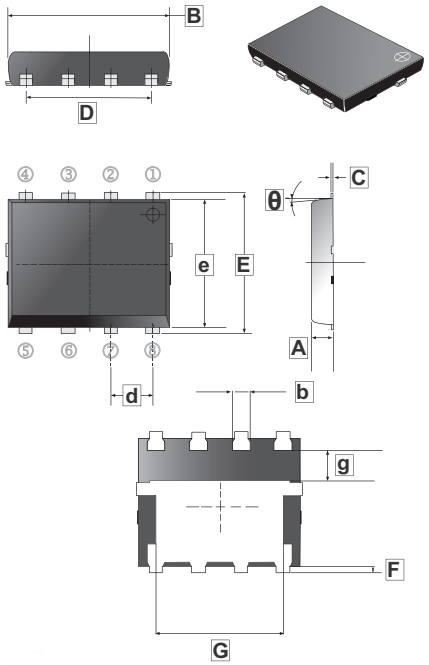
MARKING

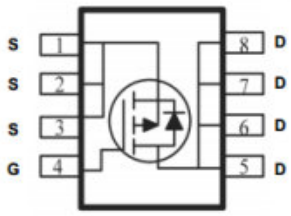


PACKAGE INFORMATION

Package	MPQ	Leader Size
PPAK5x6	3K	13 inch

PPAK5x6





REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	0.9	1.1	θ	0°	12°
B	4.9	5.1	b	0.33	0.51
C	0.2	0.3	d	1.27 BSC	
D	3.81	4	e	5.7	5.9
E	5.95	6.2	g	1.1	1.4
F	0.1	0.2			
G	3.81	4			

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current [1]	I_D @T_C=25℃	-16	A
	I_D @T_C=100℃	-10	A
Pulsed Drain Current[2]	I_{DM}	-64	A
Continuous Drain Current [1]	I_D @T_A=25℃	-5	A
	I_D @T_A=70℃	-4	A
Total Power Dissipation[4]	P_D @T_C=25℃	25	W
	P_D @T_A=25℃	2	W
Single Pulse Avalanche Energy, L=0.1mH[3]	E_{AS}	51	mJ
Single Pulse Avalanche Current, L=0.1mH[3]	I_{AS}	-32	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	℃

Thermal Data

Parameter	Symbol	Conditions	Max. Value	Unit
Thermal Resistance Junction-ambient[1]	$R_{\theta JA}$	Steady State	62.5	℃/W
Thermal Resistance Junction-case[1]	$R_{\theta JC}$	Steady State	5	℃/W

DEVICE CHARACTERISTICS

YS5465BA

Electrical Characteristics (T_J = 25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	-60	-	-	V	V_{GS}=0, I_D=-250uA
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	-1.7	-2.5	V	V_{DS}=V_{GS}, I_D=-250uA
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	I_{DSS}	-	-	-1	uA	V_{DS}=-60V, V_{GS}=0
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	-	44	48	mΩ	V_{GS}=-10V, I_D=-8A
		-	55	65		V_{GS}=-4.5V, I_D=-4A
Total Gate Charge[2]	Q_g	-	22	-	nC	I_D=-8A V_{DS}=-30V V_{GS}=-10V
Gate-Source Charge	Q_{gs}	-	4.1	-		
Gate-Drain (“Miller”) Change	Q_{gd}	-	5.2	-		
Turn-on Delay Time[2]	$T_{d(on)}$	-	13	-	ns	V_{DS}=-30V I_D=-1A V_{GS}=-10V R_G=6Ω
Rise Time	T_r	-	42	-		
Turn-off Delay Time	$T_{d(off)}$	-	65	-		
Fall Time	T_f	-	16	-		
Input Capacitance	C_{iss}	-	1256	-	pF	V_{GS}=0V V_{DS}=-30V f=1.0MHz
Output Capacitance	C_{oss}	-	87	-		
Reverse Transfer Capacitance	C_{rss}	-	59	-		

Guaranteed Avalanche Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Single Pulse Avalanche Energy[5]	EAS	3.2	-	-	mJ	V_{DD}=-25V, L=0.1mH, I_{AS}=-8A

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Diode Forward Voltage[2]	V_{SD}	-	-0.72	-1.0	V	I_S=-1A, V_{GS}=0V, T_J=25℃
Continuous Source Current[1,6]	I_S	-	-	-16	A	---

Notes: **1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.**

2. The data tested by pulsed, pulse width ≦ 300us, duty cycle ≦ 2%.

3. The EAS data shows Max. rating. The test condition is VDD=-25V, VGS=-10V, L=0.1mH, IAS=-32A.

4. The power dissipation is limited by 150℃ junction temperature.

5. The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

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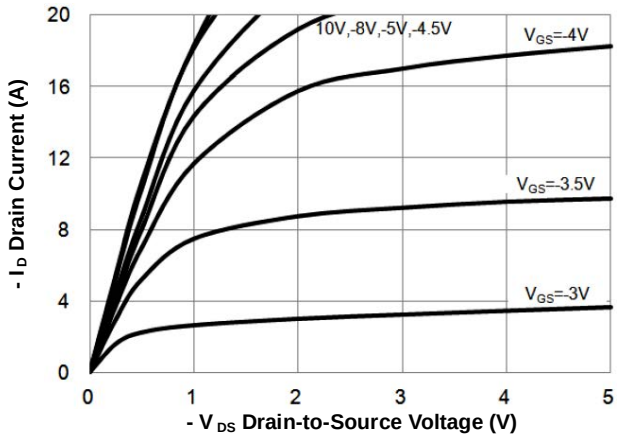

Fig.1 Typical Output Characteristics

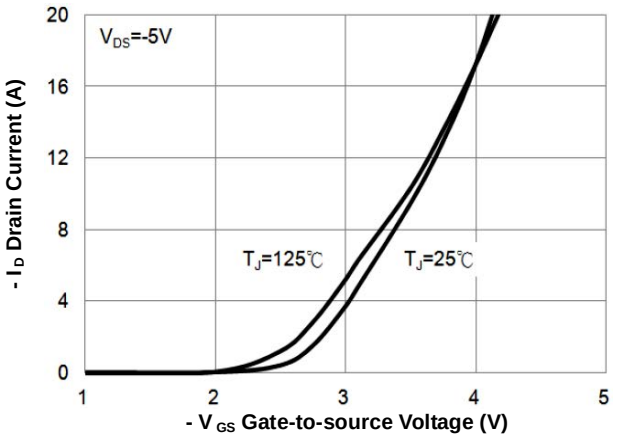

Fig.2 Transfer Characteristics

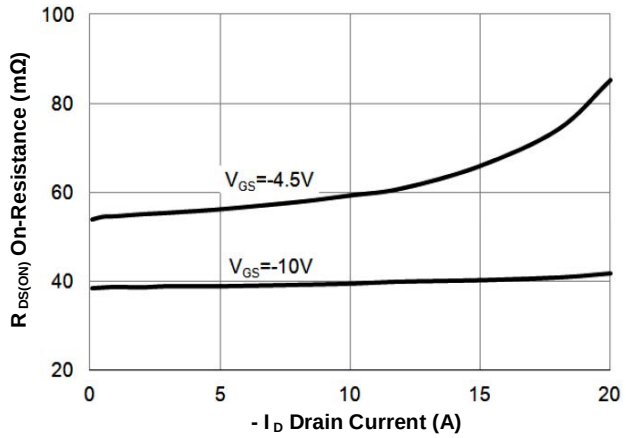

Fig.3 On-Resistance vs. Drain Current

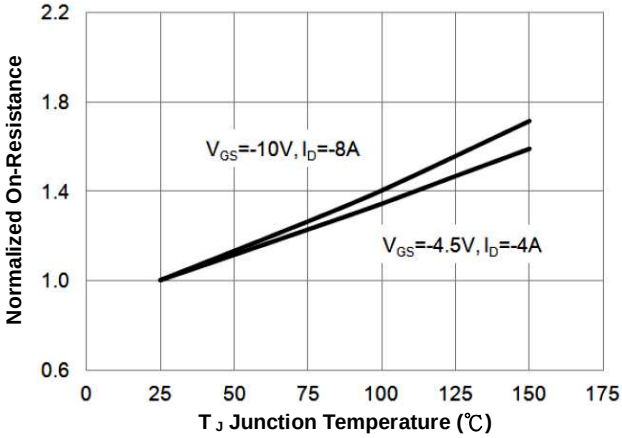

Fig.4 Normalized R_{DSON} vs. T_J

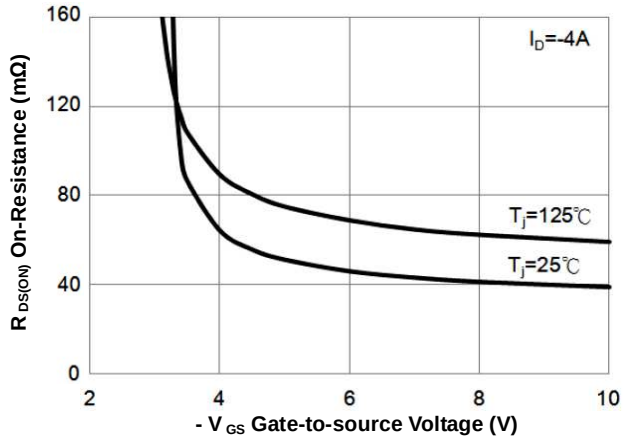

Fig.5 On-Resistance vs. G-S Voltage

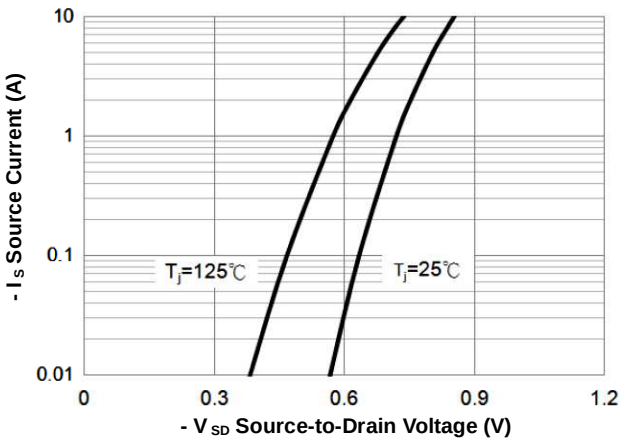

Fig.6 Forward Characteristics of Reverse

DEVICE CHARACTERISTICS

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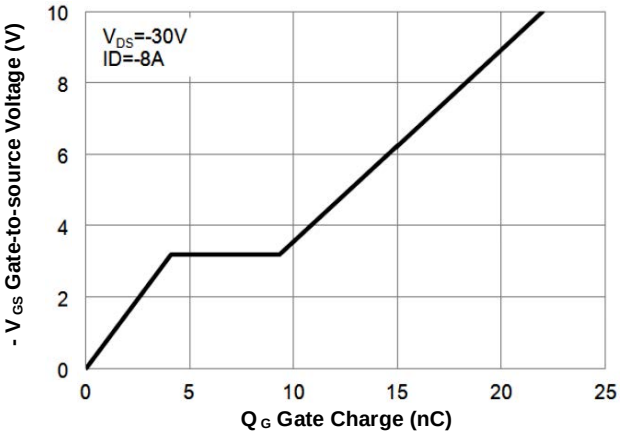

Fig.7 Gate Charge Characteristics

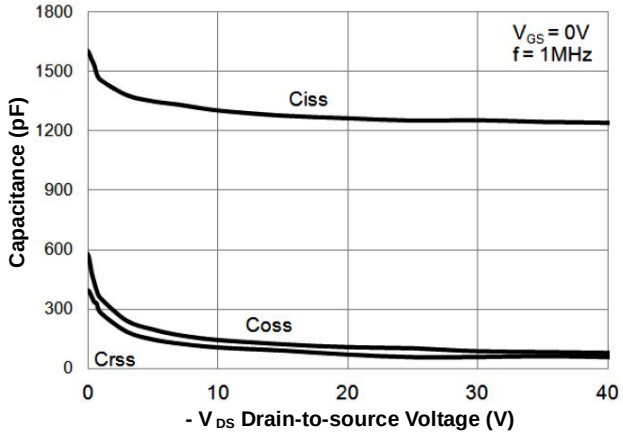

Fig.8 Capacitance Characteristics

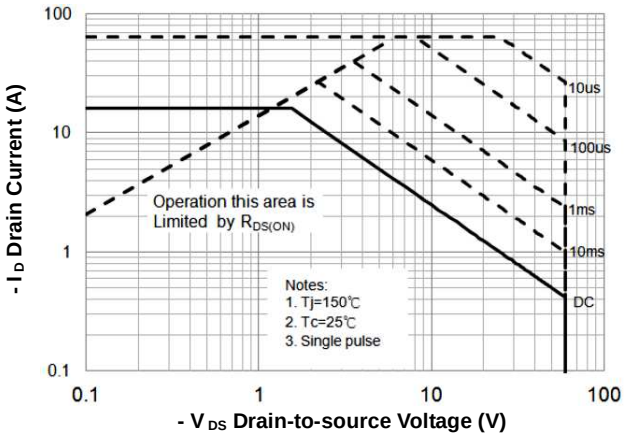

Fig.9 Safe Operating Area

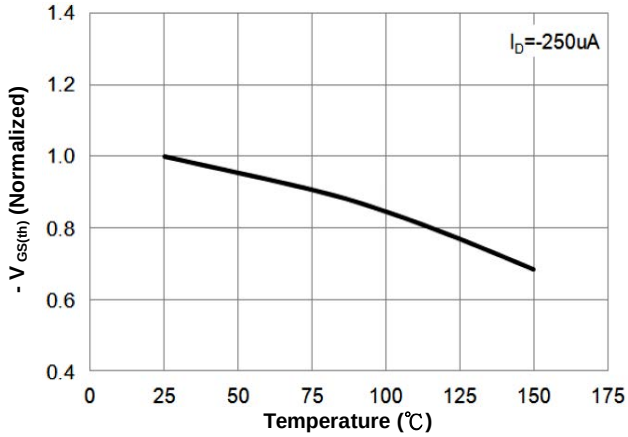

Fig.10 Normalized $V_{GS(th)}$ vs. Temperature

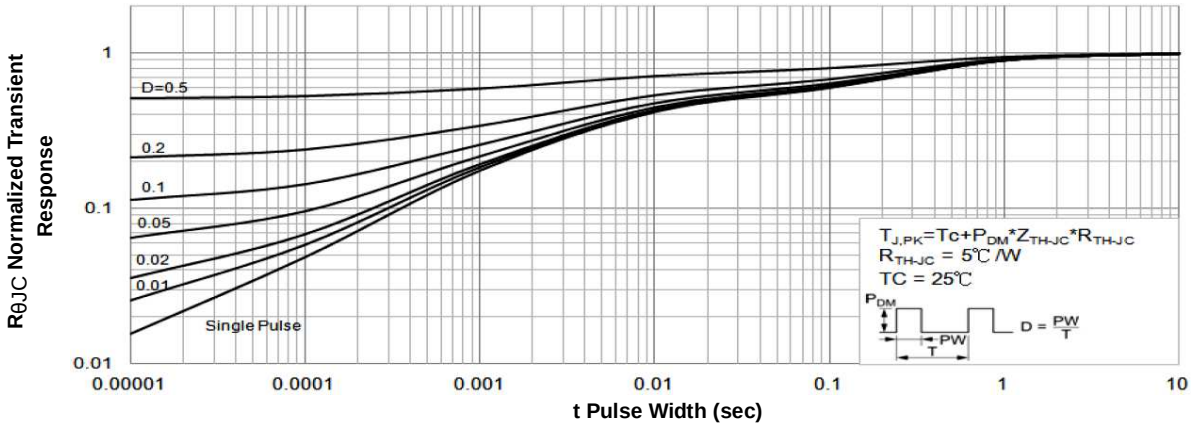

Fig.11 Normalized Maximum Transient Thermal Impedance